

# **isc** Silicon NPN Power Transistor

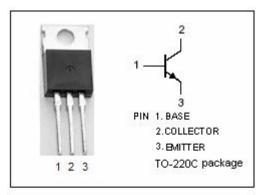
# 2SD772

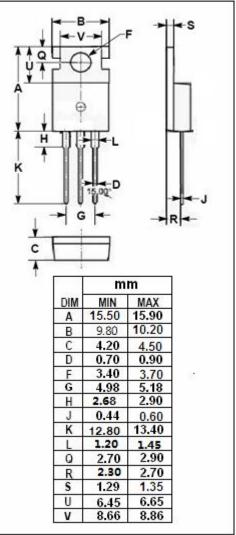
#### DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 80V(Min.)
- Collector-Emitter Saturation Voltage-
- : V<sub>CE(sat)</sub>= 1.6V(Max.) @I<sub>C</sub>= 5A
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

• Designed for power amplifier applications.





### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOLPARAMETERVALUEUNITVCBOCollector-Base Voltage150VVCESCollector-Emitter Voltage150VVCEOCollector-Emitter Voltage80VVEBOEmitter-Base Voltage6VIcCollector Current-Continuous5AICMCollector Current-Peak10A				
VCES   Collector-Emitter Voltage   150   V     VCEO   Collector-Emitter Voltage   80   V     VEBO   Emitter-Base Voltage   6   V     Ic   Collector Current-Continuous   5   A	STMBOL	PARAMETER	VALUE	UNIT
V <sub>CEO</sub> Collector-Emitter Voltage 80 V   V <sub>EBO</sub> Emitter-Base Voltage 6 V   Ic Collector Current-Continuous 5 A	V <sub>CBO</sub>	Collector-Base Voltage	150	v
V <sub>EBO</sub> Emitter-Base Voltage 6 V   Ic Collector Current-Continuous 5 A	VCES	Collector-Emitter Voltage	150	V
Ic Collector Current-Continuous 5 A	V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
	V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>CM</sub> Collector Current-Peak 10 A	lc	Collector Current-Continuous	5	A
	I <sub>CM</sub>	Collector Current-Peak	10	A
$ P_{C} \qquad \begin{array}{c} Collector \ Power \ Dissipation \\ @ \ T_{C} = 25 \ C \end{array} \qquad \begin{array}{c} 40 \qquad W \end{array} $	Pc		40	W
T <sub>J</sub> Junction Temperature 150 °C	TJ	Junction Temperature	150	°C
Tstg Storage Temperature Range -55~150 °C	T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

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## ELECTRICAL CHARACTERISTICS

### $T_{c}\text{=}25^{\circ}\!\!\!\!\!\!C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; L= 25mH	80			V
V(BR)EBO	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.6	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 5A; V <sub>CE</sub> = 4V			1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0			1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 4V	14			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		40		MHz
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 5A, I <sub>B1</sub> = 0.8A; V <sub>EB</sub> = 5V			1	μ <b>S</b>

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